

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Bojarczuk, et al.

09/755,164

Group Art Unit:

2826

Serial No.:

· Examiner:

Quinto, Kevin V.

Filed: For:

ALUMINUM NITRIDE AND ALUMINUM OXIDE/ALUMINUM NITRIDE HETEROSTRUCTURE GATE DIELECTRIC STACK BASED FIELD EFFECT

TRANSISTORS AND METHOD FOR FORMING SAME

Honorable Commissioner of Patents

Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated January 30, 2003, please amend the aboveidentified application as follows:

INTRODUCTORY COMMENTS

Claims 1-7 and 14-18 are all the claims presently pending in the application. Claims 1-7,

14-15 and 17 have been amended to more clearly define the invention and claims 8-13 and 19-27

have been canceled. Claims 1, 14-15 and 17 are independent.

TECHNOLOGY CENTER 2800